Narihito Okada

List of Publications by Year
in descending order

52 papers	679 citations	687363 13 h-index	580821 25 g-index
52 all docs	52 docs citations	52 times ranked	658 citing authors

#	Article	IF	Citations
1	Three-dimensional curving of crystal planes in wide bandgap semiconductor wafers visualized using a laboratory X-ray diffractometer. Journal of Crystal Growth, 2022, 583, 126558.	1.5	2
2	Investigation of off-cut angle of sapphire for epitaxial lateral overgrowth of AlN and fabrication of high-quality AlN template. Journal of Crystal Growth, 2022, 588, 126640.	1.5	6
3	Observation of threading dislocations with a c+m type Burgers vector in HVPE GaN substrates using multi-photon excitation photoluminescence and TEM. Journal of Crystal Growth, 2022, , 126748.	1.5	0
4	Study on higher-energy emission observed locally around V-pits on InGaN/GaN quantum wells grown on moderate-temperature GaN. Journal of Applied Physics, 2021, 130, 053103.	2.5	0
5	Deep ultraviolet emission from multiple quantum wells on flat N-polar AlN templates fabricated using periodical pulsed H₂ etching. Japanese Journal of Applied Physics, 2021, 60, 125502.	1.5	4
6	Anisotropic radius of curvature of crystal planes in wide-bandgap semiconductor wafers measured by X-ray diffraction. Japanese Journal of Applied Physics, 2021, 60, 128004.	1.5	2
7	Correlation between structural properties and nonradiative recombination behaviors of threading dislocations in freestanding GaN substrates grown by hydride vapor phase epitaxy. CrystEngComm, 2020, 22, 8299-8312.	2.6	13
8	Study of dislocations in AlN single-crystal using bright-field synchrotron x-ray topography under a multiple-beam diffraction condition. Applied Physics Letters, 2020, 117, 092102.	3.3	4
9	Growth and Characterization of Nitrogenâ€Polar AlGaN/AlN Heterostructure for Highâ€Electronâ€Mobility Transistor. Physica Status Solidi (B): Basic Research, 2020, 257, 1900589.	1.5	13
10	Effect of InGaN/GaN Superlattice on Lattice Curvature of GaN Layers Grown on Sapphire Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900586.	1.5	1
11	Growth of Nâ€Polar Aluminum Nitride on Vicinal Sapphire Substrates and Aluminum Nitride Bulk Substrates. Physica Status Solidi (B): Basic Research, 2020, 257, 1900588.	1.5	17
12	High-quality GaN crystals grown from double-polarity hydride vapor phase epitaxy and single-polarization regrowth. Japanese Journal of Applied Physics, 2019, 58, SC1019.	1.5	0
13	Growth of GaN and improvement of lattice curvature using symmetric hexagonal SiO₂ patterns in HVPE growth. Japanese Journal of Applied Physics, 2019, 58, SC1049.	1.5	6
14	Observation of dislocations and their arrays in physical vapor transport-grown AlN single-crystal substrate by synchrotron X-ray topography. Japanese Journal of Applied Physics, 2019, 58, SCCB29.	1.5	10
15	Effect of off-angle of stripe patterns on facet stability and embedding in selective-area hydride vapor phase epitaxy growth. Japanese Journal of Applied Physics, 2019, 58, SC1001.	1.5	0
16	Separation of effects of InGaN/GaN superlattice on performance of light-emitting diodes using mid-temperature-grown GaN layer. Japanese Journal of Applied Physics, 2018, 57, 062101.	1.5	13
17	Spatially Resolved Spectroscopy of Blue and Green InGaN Quantum Wells by Scanning Nearâ€Field Optical Microscopy. Physica Status Solidi (B): Basic Research, 2018, 255, 1700322.	1.5	3
18	Potential Barrier Formed Around Dislocations in InGaN Quantum Well Structures by Spot Cathodoluminescence Measurements. Physica Status Solidi (B): Basic Research, 2018, 255, 1700358.	1.5	13

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19	Impact of thermal treatment on the growth of semipolar AlN on m-plane sapphire. AIP Advances, 2018, 8, .	1.3	12
20	Nanoscopic spectroscopy of potential barriers formed around V-pits in InGaN/GaN multiple quantum wells on moderate temperature GaN pit expansion layers. Journal of Applied Physics, 2018, 124, .	2.5	7
21	Mechanism for the formation of nitrogen-filled voids after annealing of GaN on a sapphire substrate. Journal of Applied Physics, 2018, 124, .	2.5	4
22	Direct observation of inclined a-type threading dislocation with a-type screw dislocation in GaN. Journal of Applied Physics, 2017, 121, 185101.	2.5	7
23	Visualization of dislocation behavior in HVPEâ€grown GaN using facet controlling techniques. Physica Status Solidi (B): Basic Research, 2017, 254, 1600716.	1.5	6
24	Bulk GaN substrate with overall dislocation density on the order of 105/cm2 fabricated by hydride vapor phase epitaxy. Journal of Crystal Growth, 2017, 478, 123-128.	1.5	21
25	V-shaped pits in HVPE-grown GaN associated with columnar inversion domains originating from foreign particles of Î±-Si3N4 and graphitic carbon. Micron, 2017, 94, 9-14.	2.2	4
26	Alternately doubleâ€sided growth of lowâ€curvature GaN templates on sapphire substrates using hydride vapor phase epitaxy. Physica Status Solidi (B): Basic Research, 2016, 253, 819-823.	1.5	3
27	Origin of lattice bowing of freestanding GaN substrates grown by hydride vapor phase epitaxy. Journal of Applied Physics, 2016, 119, .	2.5	16
28	Growth of semipolar {20â€“21} GaN and {20â€“2â€“1} GaN for GaN substrate. Physica Status Solidi (B): Basic Research, 2016, 253, 36-45.	1.5	1
29	Effect of superlattice on light output power of InGaNâ€based lightâ€emitting diodes fabricated on underlying GaN substrates with different dislocation densities. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 270-273.	0.8	5
30	Thickness and growth condition dependence of crystallinity in semipolar (20â€“21) GaN films grown on (22â€“43) patterned sapphire substrates. Physica Status Solidi (B): Basic Research, 2015, 252, 1142-1148.	1.5	5
31	Crystalline property analysis of semipolar (20â€“21) GaN on (22â€“43) patterned sapphire substrate by Xâ€ray microdiffraction and transmission electron microscopy. Physica Status Solidi (B): Basic Research, 2015, 252, 1149-1154.	1.5	6
32	Controlling potential barrier height by changing V-shaped pit size and the effect on optical and electrical properties for InGaN/GaN based light-emitting diodes. Journal of Applied Physics, 2015, 117, .	2.5	40
33	WeC-2-1 Transmission electron microscopy study on origin of threading dislocations in GaN layer grown on patterned sapphire substrate. Proceedings of JSME-IIP/ASME-ISPS Joint Conference on Micromechatronics for Information and Precision Equipment IIP/ISPS Joint MIPE, 2015, 2015, WeC-2-1-1- WeC-2-1-3.	0.0	0
34	Fabrication of freestanding {20$ ar 2 $1} GaN substrates by HVPE using SiO₂ masked GaN templates. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 401-404.	0.8	6
35	Epitaxial lateral overgrowth of thick semipolar {11$ ar 2 $2} GaN by hydride vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 549-552.	0.8	0
36	Characterization of semipolar {11$ ar 2 $2} light-emitting diodes using a hole blocking layer. Physica Status Solidi C: Current Topics in Solid State Physics, 2014, 11, 775-777.	0.8	2

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37	S1660104 Optimal design of the patterned sapphire substrate from viewpoints of light extraction efficiency and crystalline quality of light emitting diodes. The Proceedings of Mechanical Engineering Congress Japan, 2014, 2014, _S1660104--_S1660104-.	0.0	0
38	I-1-3 Etching of nano-patterned sapphire substrates using chf_3 and BCl_3 inductively coupled plasmas. The Proceedings of the Conference on Information Intelligence and Precision Equipment IIP, 2013, 2013, 8-12.	0.0	0
39	Green lightâ€emitting diodes fabricated on semipolar (11â€“22) GaN on râ€plane patterned sapphire substrate. Physica Status Solidi (A) Applications and Materials Science, 2012, 209, 469-472.	1.8	21
40	Growth of {11â€22} GaN on shallowly etched r â€plane patterned sapphire substrates. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 568-571.	0.8	8
41	Behavior of misfit dislocations in semipolar InGaN/GaN grown by MOVPE. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 488-491.	0.8	6
42	Growth of semipolar {10$ ar 1 $1} GaN from c -plane-like sapphire sidewall of patterned n -plane sapphire substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 2101-2103.	0.8	15
43	Characterization of semipolar (11$ ar 2 $2) GaN on c -plane sapphire sidewall of patterned r -plane sapphire substrate without SiO2 mask. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2059-2062.	0.8	5
44	Evaluation of multipleâ€quantumâ€well structure on InGaN template using (11$ ar 2 $2) facet growth and mass transport. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2063-2065.	0.8	4
45	Growth mechanism of nonpolar m -plane GaN on maskless patterned a -plane sapphire substrate. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2066-2068.	0.8	2
46	Lightâ€emitting diodes fabricated on nanopatterned sapphire substrates by thermal lithography. Physica Status Solidi C: Current Topics in Solid State Physics, 2010, 7, 2165-2167.	0.8	15
47	Growth of m â€GaN layers by epitaxial lateral overgrowth from sapphire sidewalls. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1164-1167.	1.8	12
48	High-efficiency AlGaN-based UV light-emitting diode on laterally overgrown AlN. Journal of Crystal Growth, 2008, 310, 2326-2329.	1.5	54
49	Impact of high-temperature growth by metal-organic vapor phase epitaxy on microstructure of AlN on 6H-SiC substrates. Journal of Crystal Growth, 2008, 310, 2308-2313.	1.5	65
50	Dislocations in AlN Epilayers Grown on Sapphire Substrate by High-Temperature Metal-Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2007, 46, 1458-1462.	1.5	90
51	Epitaxial lateral overgrowth of AlN on trench-patterned AlN layers. Journal of Crystal Growth, 2007, 298, 257-260.	1.5	104
52	Thermodynamic Aspects of Growth of AlGaN by High-Temperature Metal Organic Vapor Phase Epitaxy. Japanese Journal of Applied Physics, 2006, 45, 2502-2504.	1.5	26